

Pk Hurley

List of Publications by Year in descending order

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15
papers

612
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1040056

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15
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15
docs citations

15
times ranked

721
citing authors

#	ARTICLE	IF	CITATIONS
1	Nanocrystalline TiO ₂ films studied by optical, XRD and FTIR spectroscopy. Journal of Non-Crystalline Solids, 2002, 303, 134-138.	3.1	163
2	Navigation aids in the search for future high-k dielectrics: Physical and electrical trends. Solid-State Electronics, 2007, 51, 622-626.	1.4	124
3	Determination of electron effective mass and electron affinity in HfO ₂ using MOS and MOSFET structures. Solid-State Electronics, 2009, 53, 438-444.	1.4	102
4	Interface of ultrathin HfO ₂ films deposited by UV-photo-CVD. Thin Solid Films, 2004, 453-454, 203-207.	1.8	56
5	Investigation of TiO ₂ -doped HfO ₂ thin films deposited by photo-CVD. Thin Solid Films, 2003, 428, 263-268.	1.8	50
6	Characterisation of HfO ₂ deposited by photo-induced chemical vapour deposition. Thin Solid Films, 2003, 427, 391-396.	1.8	35
7	High-k-oxide/silicon interfaces characterized by capacitance frequency spectroscopy. Solid-State Electronics, 2008, 52, 1274-1279.	1.4	27
8	The influence of HfO ₂ film thickness on the interface state density and low field mobility of n channel HfO ₂ /TiN gate MOSFETs. Microelectronic Engineering, 2007, 84, 1874-1877.	2.4	19
9	Scaling potential and MOSFET integration of thermally stable Gd silicate dielectrics. Microelectronic Engineering, 2009, 86, 1642-1645.	2.4	15
10	Photo-Induced CVD of Tantalum Pentoxide Dielectric Films Using an Injection Liquid Source. Materials Research Society Symposia Proceedings, 1999, 567, 397.	0.1	9
11	Gentle FUSI NiSi metal gate process for high-k dielectric screening. Microelectronic Engineering, 2008, 85, 2019-2021.	2.4	7
12	Post deposition UV-induced O ₂ annealing of HfO ₂ thin films. Microelectronics Reliability, 2005, 45, 957-960.	1.7	4
13	Thermally activated analysis of LaSiO _x /Si and GdSiO _x /Si structures at cryogenic temperatures. Microelectronic Engineering, 2013, 109, 31-34.	2.4	1
14	Transport and interface states in high- $\hat{\rho}$ LaSiO _x dielectric. Microelectronic Engineering, 2011, 88, 1342-1345.	2.4	0
15	Electrical Properties of High- $\hat{\rho}$; K $\hat{\rho}$; LaLuO $\hat{\rho}$;3 $\hat{\rho}$; Gate Oxide for SOI MOSFETs. Advanced Materials Research, 0, 276, 87-93.	0.3	0